Remarks

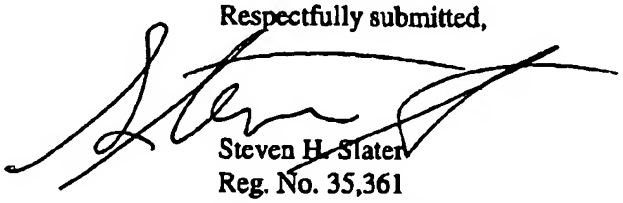
Claims 1, 3, 6, and 7 were rejected as being anticipated by U.S. Patent Application Publication 2002/0074598 to Doyle, et al. ("Doyle"). Applicants respectfully traverse the rejection on the following grounds. Claim 1 recites a transistor having a source region, a drain region and "an impurity region . . . laterally spaced from the source and drain regions." Examiner has asserted that Doyle discloses this feature, "as can be seen in the figure." Applicants respectfully respond that the figures of Doyle do not disclose this feature. Figures 5 – 7, for instance, illustrate a method of forming an NMOS device. As can be seen in Figure 7, the voids 56 of Doyle are aligned with the source and drain regions 58 and 60, respectively. This is consistent with the description of the figures, which states that "a mask 52 is formed on a substrate 50 using conventional photoresist techniques, such that the region of the substrate 50 that will eventually be the channel region of NMOS device is exposed (see FIG. 5). Then, helium is implanted to form voids 56 in the exposed region." See Doyle at Paragraph 39 (emphasis added). As Doyle describes, the voids are formed in the channel region, which clearly is aligned with and abuts the source and drain regions (see Figure 7). As such, the impurity region of Doyle is not laterally spaced from the source and drain regions.

Figures 8-10 of Doyle illustrate a method of forming a PMOS. As the figures illustrate, the impurity region is formed directly beneath the source and drain regions, and hence is not formed laterally spaced from the source and drain regions, as required by claim 1. Other figures in Doyle show that the impurity region either abuts the source and drain regions (e.g., Figure 11 and Figure 18) or underlies the source and/or drain region (Figure 12). Nowhere does Doyle teach or suggest, however, forming the impurity region in the channel region and laterally spaced from the source and drain regions. For at least this reason, claim 1 and by dependence claims 2-12 are patentably distinct over the prior art.

Because Doyle fails to anticipate or render obvious claim 1, Applicants will not address herein the additional distinguishing features of dependent claims 2-12 over the prior art. Applicants' failure to do so should not be interpreted as agreement with Examiner's assertion, however, and Applicants reserve the right to raise such distinguishing features, however, should Examiner raise additional or other grounds for rejection.

Applicants respectfully request reconsideration and withdrawal of the rejection of pending claims 1-12 and that the present application be promptly passed to issuance.

Respectfully submitted,



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